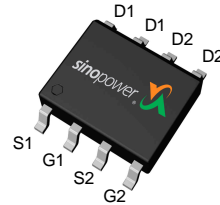


Dual P-Channel Enhancement Mode MOSFET

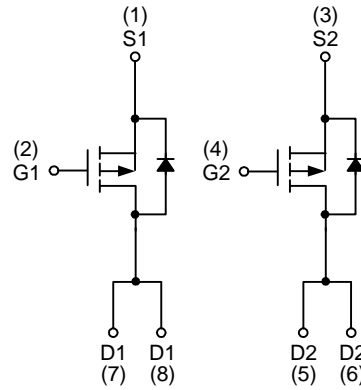
Features

- 30V/-9A,
 $R_{DS(ON)} = 15m\Omega$ (typ.) @ $V_{GS} = -10V$
 $R_{DS(ON)} = 28m\Omega$ (typ.) @ $V_{GS} = -4.5V$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

Pin Description



Top View of SOP-8



P-Channel MOSFET

Applications

- Power Management in MB/NB DC-DC Converter Application.

Ordering and Marking Information

<p>APM4927 □□-□□ □</p> <p>Assembly Material Handling Code Temperature Range Package Code</p>	<p>Package Code K : SOP-8 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel Assembly Material G : Halogen and Lead Free Device</p>		
<p>APM4927 K :</p>	<table border="1"> <tr> <td data-bbox="430 1568 574 1657"> APM4927 XXXXX ● </td> <td data-bbox="574 1568 1425 1657"> XXXXX - Date Code </td> </tr> </table>	APM4927 XXXXX ●	XXXXX - Date Code
APM4927 XXXXX ●	XXXXX - Date Code		

Note : SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit	
V_{DSS}	Drain-Source Voltage	-30	V	
V_{GSS}	Gate-Source Voltage	± 25		
I_D^a	Continuous Drain Current	$T_A=25^\circ\text{C}$	-9	A
		$T_A=70^\circ\text{C}$	-7.5	
I_{DM}^a	Pulsed Drain Current	$V_{GS}=-10\text{V}$	-35	
I_S^a	Diode Continuous Forward Current		-2.5	
I_{AR}^b	Avalanche Current		-25	
E_{AR}^b	Repetitive Avalanche Energy (L=0.3mH)		94	mJ
T_J	Maximum Junction Temperature		150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range		-55 to 150	
P_D^a	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	2.5	W
		$T_A=70^\circ\text{C}$	1.6	
$R_{\theta JA}^{a,c}$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	50	$^\circ\text{C/W}$
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	Steady State	25	

Note a : Surface Mounted on 1in^2 pad area, $t \leq 10\text{sec}$.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^\circ\text{C}$).

Note c : Maximum under Steady State conditions is 75°C/W .

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	APM4927K			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_{DS}=-250\mu\text{A}$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}, V_{GS}=0\text{V}$ $T_J=85^\circ\text{C}$	-	-	-1	μA
			-	-	-30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=-250\mu\text{A}$	-1	-2	-2.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 25\text{V}, V_{DS}=0\text{V}$	-	-	± 100	nA
$R_{DS(ON)}^d$	Drain-Source On-state Resistance	$V_{GS}=-10\text{V}, I_{DS}=-9\text{A}$	-	15	19	m Ω
		$V_{GS}=-4.5\text{V}, I_{DS}=-6.5\text{A}$	-	28	37	
Diode Characteristics						
V_{SD}^d	Diode Forward Voltage	$I_{SD}=-2.5\text{A}, V_{GS}=0\text{V}$	-	-0.75	-1.1	V
t_{rr}^e	Reverse Recovery Time	$I_{SD}=-9\text{A}, dI_{SD}/dt=100\text{A}/\mu\text{s}$	-	20	-	ns
Q_{rr}^e	Reverse Recovery Charge		-	11	-	nC

Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

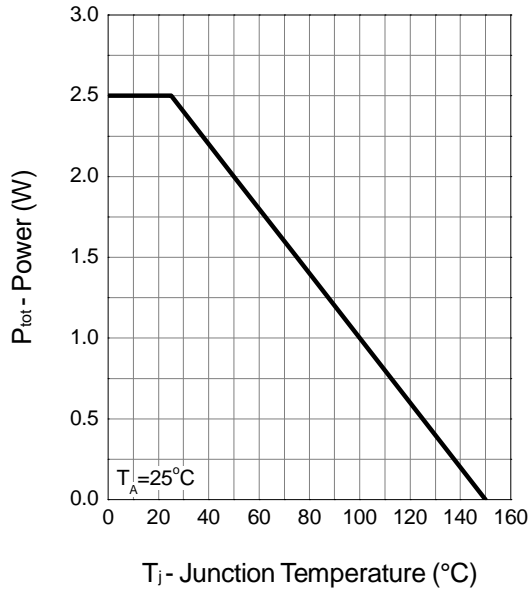
Symbol	Parameter	Test Conditions	APM4927K			Unit
			Min.	Typ.	Max.	
Dynamic Characteristics^e						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	3	5	7	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=-15V,$ Frequency=1.0MHz	-	2070	-	pF
C_{oss}	Output Capacitance		-	320	-	
C_{riss}	Reverse Transfer Capacitance		-	250	-	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=-15V, R_L=15\Omega,$ $I_{DS}=-1A, V_{GEN}=-10V,$ $R_G=6\Omega$	-	13	24	ns
t_r	Turn-on Rise Time		-	13	24	
$t_{d(OFF)}$	Turn-off Delay Time		-	59	107	
t_f	Turn-off Fall Time		-	29	53	
Gate Charge Characteristics^e						
Q_g	Total Gate Charge	$V_{DS}=-15V, V_{GS}=-10V,$ $I_{DS}=-9A$	-	35	50	nC
Q_{gs}	Gate-Source Charge		-	4.7	-	
Q_{gd}	Gate-Drain Charge		-	9.3	-	

Note d : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

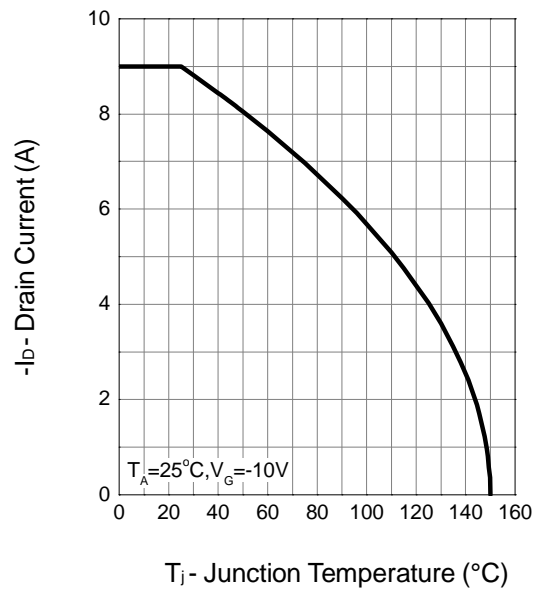
Note e : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

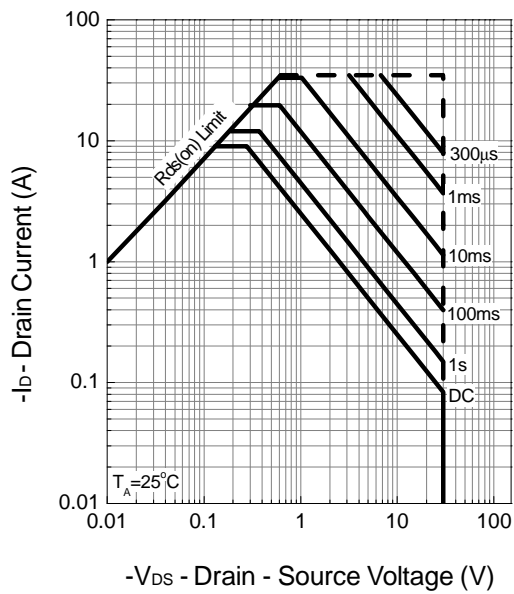
Power Dissipation



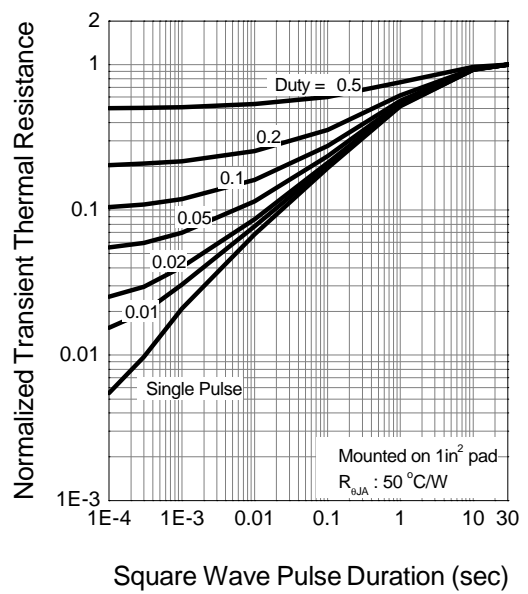
Drain Current



Safe Operation Area

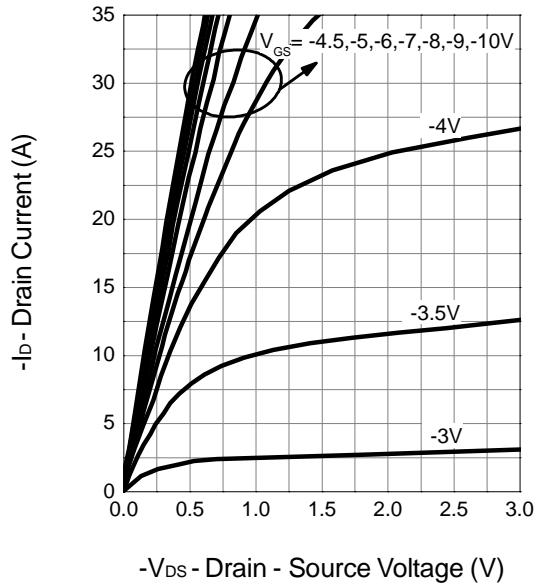


Thermal Transient Impedance

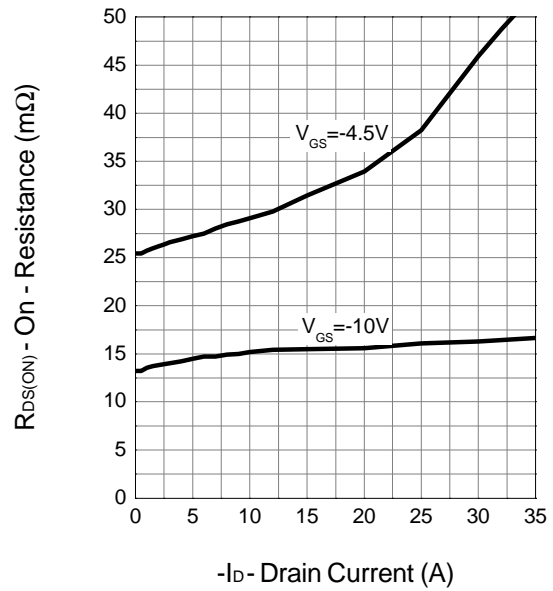


Typical Operating Characteristics (Cont.)

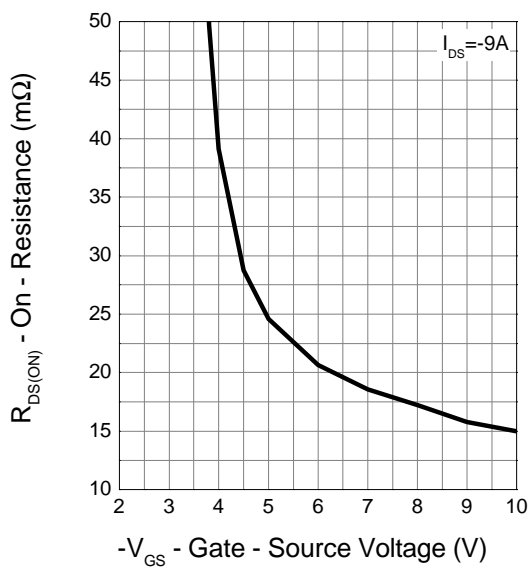
Output Characteristics



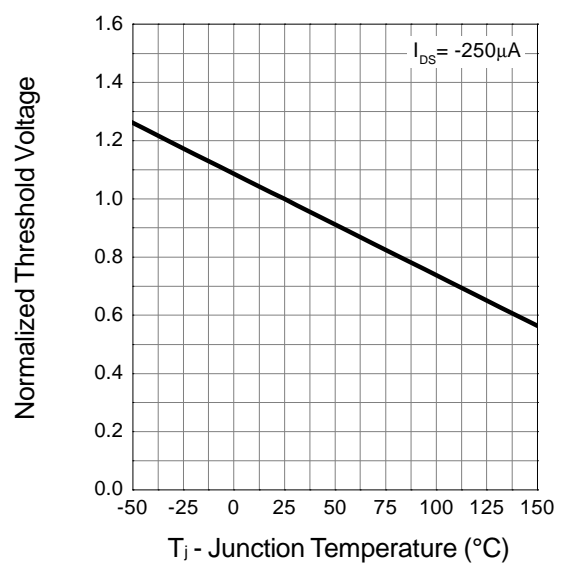
Drain-Source On Resistance



Gate-Source On Resistance

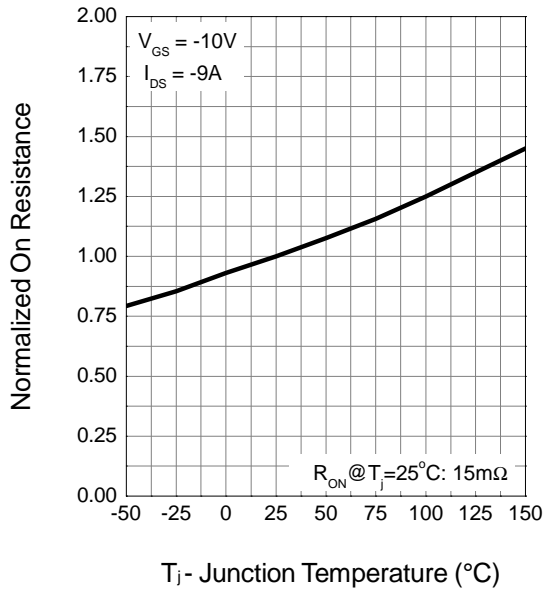


Gate Threshold Voltage

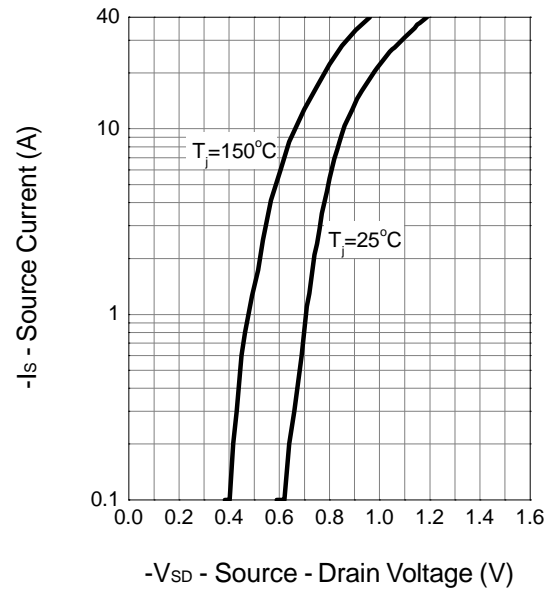


Typical Operating Characteristics (Cont.)

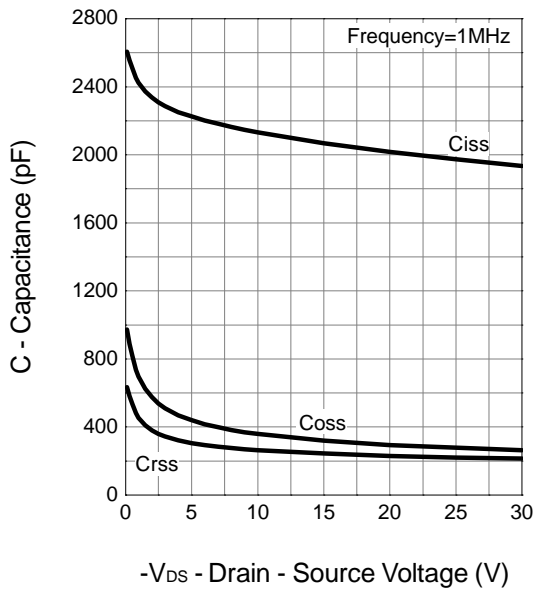
Drain-Source On Resistance



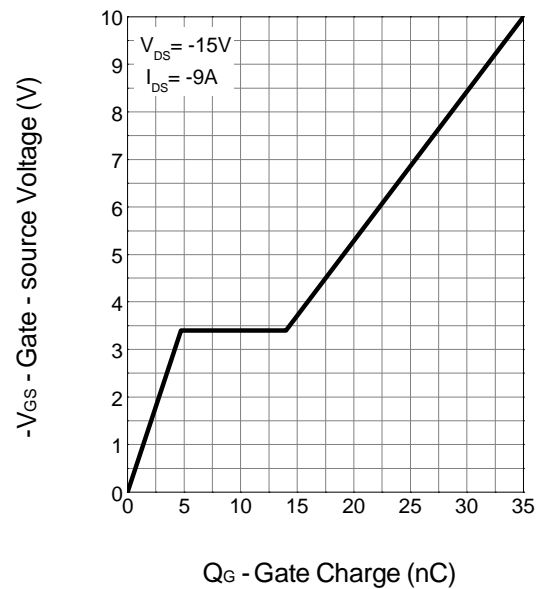
Source-Drain Diode Forward



Capacitance

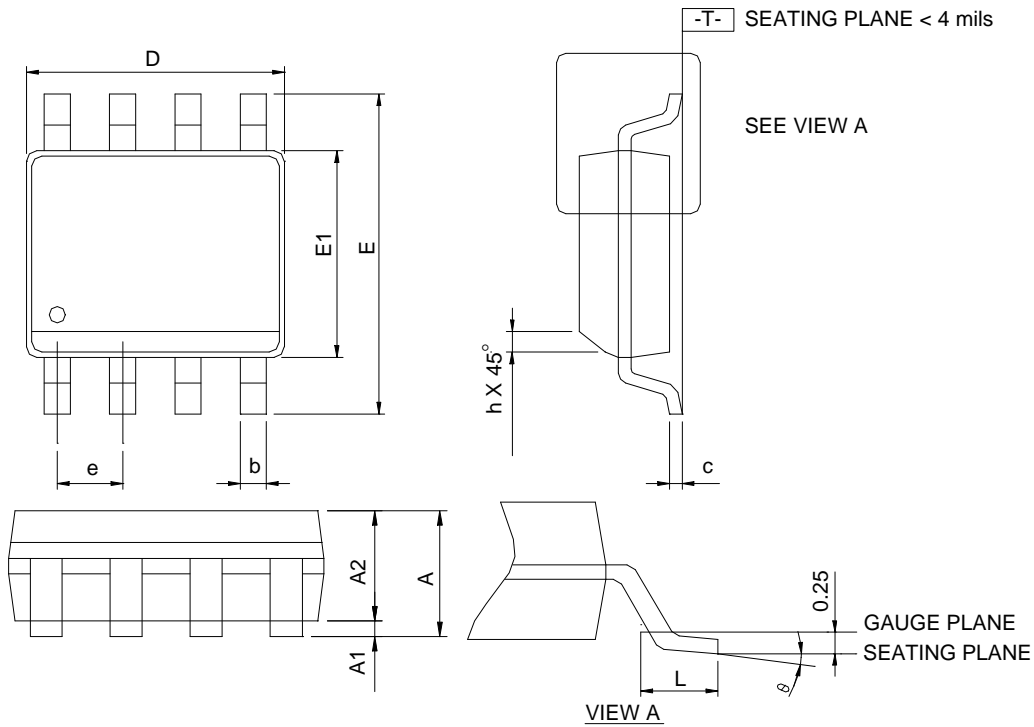


Gate Charge



Package Information

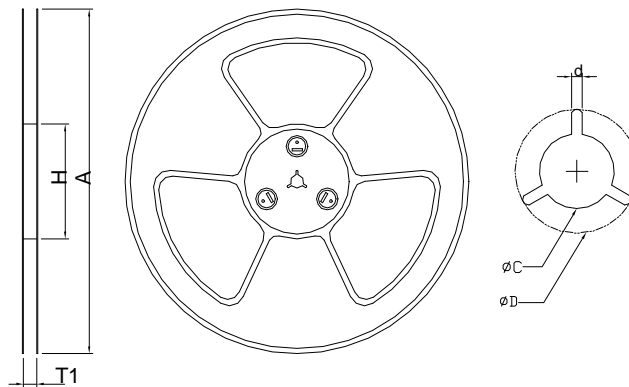
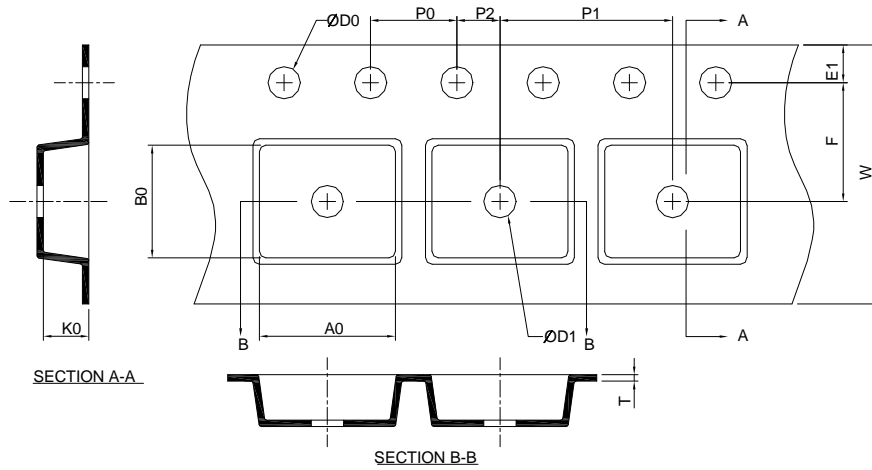
SOP-8



SYMBOL	SOP-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A		1.75		0.069
A1	0.10	0.25	0.004	0.010
A2	1.25		0.049	
b	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°

- Note: 1. Follow JEDEC MS-012 AA.
 2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
 3. Dimension "E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.

Carrier Tape & Reel Dimensions



Application	A	H	T1	C	d	D	W	E1	F
SOP-8	330.0 ±0.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0 ±0.30	1.75 ±0.10	5.5 ±0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0 ±0.10	8.0 ±0.10	2.0 ±0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.40 ±0.20	5.20 ±0.20	2.10 ±0.20

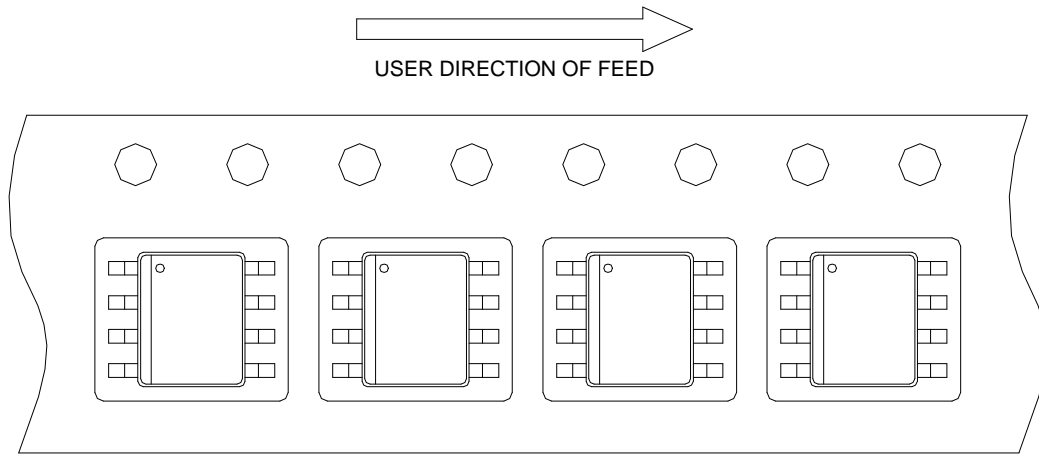
(mm)

Devices Per Unit

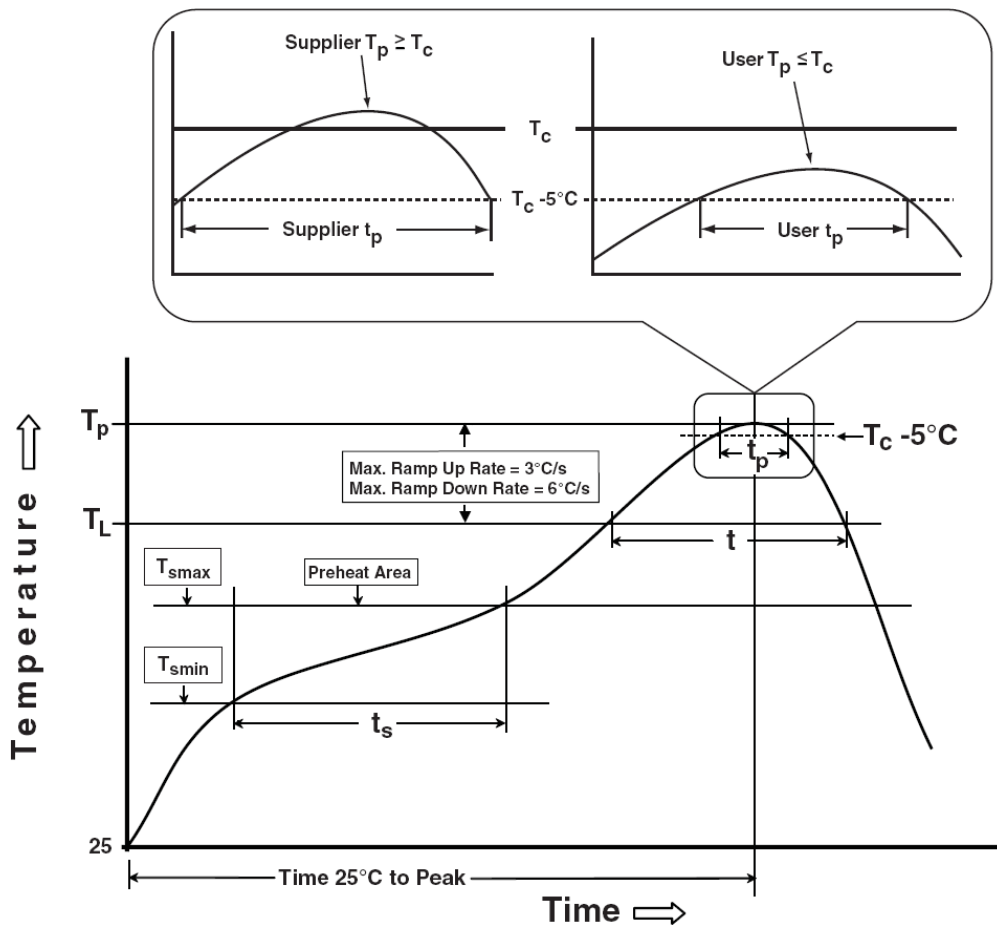
Package Type	Unit	Quantity
SOP-8	Tape & Reel	2500

Taping Direction Information

SOP-8



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HOLT	JESD-22, A108	1000 Hrs, Bias @ 125°C
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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